

In the Abstract:

~~Integrated field-effect transistor with two control regions, use of this field-effect transistor and fabrication method~~

~~An explanation is given of, inter alia, a field-effect transistor (10) fabricated as a so-called double-gate transistor (10) using the SOI technique and the salicide technique. The transistor (10) is suitable for switching voltages of greater than five volts or even greater than nine volts and requires only a very small chip area.~~

~~(Figure 1)~~

An integrated field-effect transistor is described in which a substrate region is surrounded by: two terminal regions (a source region and a drain region), two electrically insulating insulating layers, two electrically insulating regions, and an electrically conductive connecting region. The insulating layers are arranged at mutually opposite sides of the substrate region and are adjoined by control regions. The insulating regions are arranged at mutually opposite sides of the substrate region. The electrically conductive connecting region produces an electrically conductive connection between one terminal region and the substrate region. The connecting region includes a metal-semiconductor compound. Part of a covering area of the substrate region is covered by the connecting region, which extends further over a covering area of the source region. The part of the covering area of the substrate region covers the substrate region between the two insulating layers and between the two control regions.